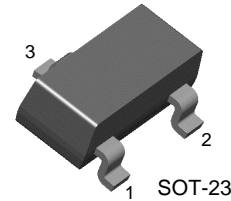


BC856/857/858/859/860

Switching and Amplifier Applications

- Suitable for automatic insertion in thick and thin-film circuits
- Low Noise: BC859, BC860
- Complement to BC846 ... BC850



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: BC856	-80	V
	: BC857/860	-50	V
	: BC858/859	-30	V
V_{CEO}	Collector-Emitter Voltage		
	: BC856	-65	V
	: BC857/860	-45	V
	: BC858/859	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_{C}	Collector Current (DC)	-100	mA
P_{C}	Collector Power Dissipation	310	mW
T_{J}	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
I_{CBO}	Collector Cut-off Current	$V_{\text{CB}} = -30\text{V}, I_{\text{E}} = 0$			-15	nA
h_{FE}	DC Current Gain	$V_{\text{CE}} = -5\text{V}, I_{\text{C}} = -2\text{mA}$	110		800	
$V_{\text{CE}}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_{\text{C}} = -10\text{mA}, I_{\text{B}} = -0.5\text{mA}$		-90	-300	mV
		$I_{\text{C}} = -100\text{mA}, I_{\text{B}} = -5\text{mA}$		-250	-650	mV
$V_{\text{BE}}(\text{sat})$	Base-Emitter Saturation Voltage	$I_{\text{C}} = -10\text{mA}, I_{\text{B}} = -0.5\text{mA}$		-700		mV
		$I_{\text{C}} = -100\text{mA}, I_{\text{B}} = -5\text{mA}$		-900		mV
$V_{\text{BE}}(\text{on})$	Base-Emitter On Voltage	$V_{\text{CE}} = -5\text{V}, I_{\text{C}} = -2\text{mA}$	-600	-660	-750	mV
		$V_{\text{CE}} = -5\text{V}, I_{\text{C}} = -10\text{mA}$			-800	mV
f_{T}	Current Gain Bandwidth Product	$V_{\text{CE}} = -5\text{V}, I_{\text{C}} = -10\text{mA}$ $f = 100\text{MHz}$		150		MHz
C_{ob}	Output Capacitance	$V_{\text{CB}} = -10\text{V}, I_{\text{E}} = 0, f = 1\text{MHz}$			6	pF
NF	Noise Figure	: BC856/857/858	$V_{\text{CE}} = -5\text{V}, I_{\text{C}} = -200\mu\text{A}$	2	10	dB
		: BC859/860	$f = 1\text{KHz}, R_{\text{G}} = 2\text{K}\Omega$	1	4	dB
		: BC859	$V_{\text{CE}} = -5\text{V}, I_{\text{C}} = -200\mu\text{A}$	1.2	4	dB
		: BC860	$R_{\text{G}} = 2\text{K}\Omega, f = 30 \sim 15000\text{Hz}$	1.2	2	dB

h_{FE} Classification

Classification	A	B	C
h_{FE}	110 ~ 220	200 ~ 450	420 ~ 800

Marking Code

Type	856A	856B	856C	857A	857B	857C	858A	858B	858C
Mark	9AA	9AB	9AC	9BA	9BB	9BC	9CA	9CB	9CC
Type	859A	859B	859C	860A	860B	860C			
Mark	9DA	9DB	9DC	9EA	9EB	9EC			

Typical Characteristics

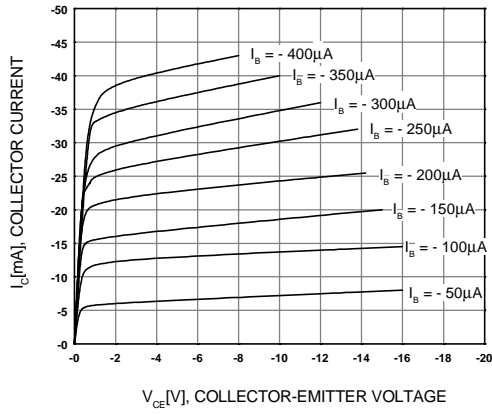


Figure 1. Static Characteristic

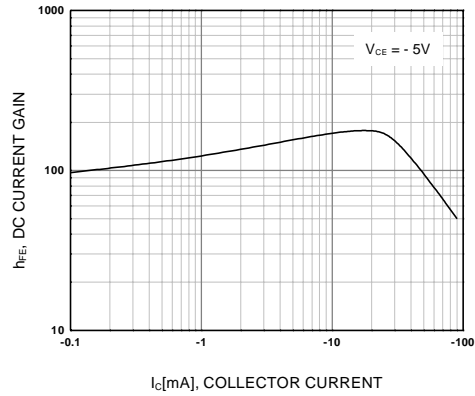


Figure 2. DC current Gain

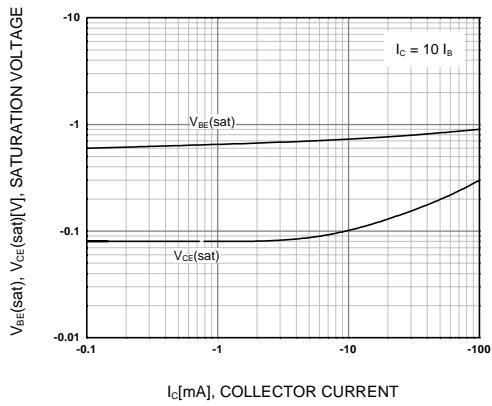


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

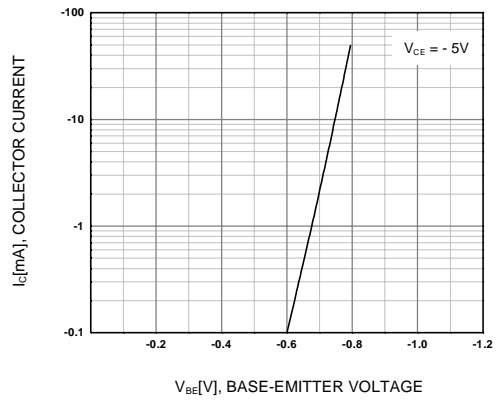


Figure 4. Base-Emitter On Voltage

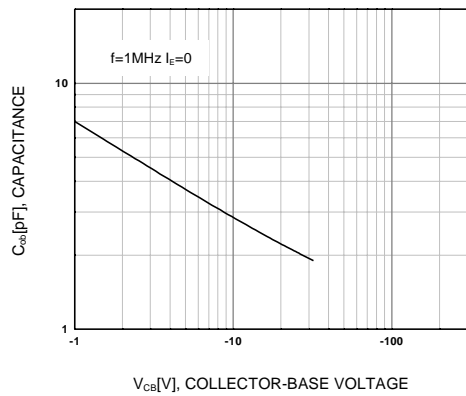


Figure 5. Collector Output Capacitance

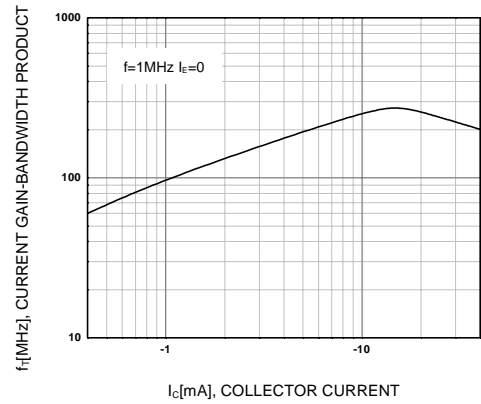
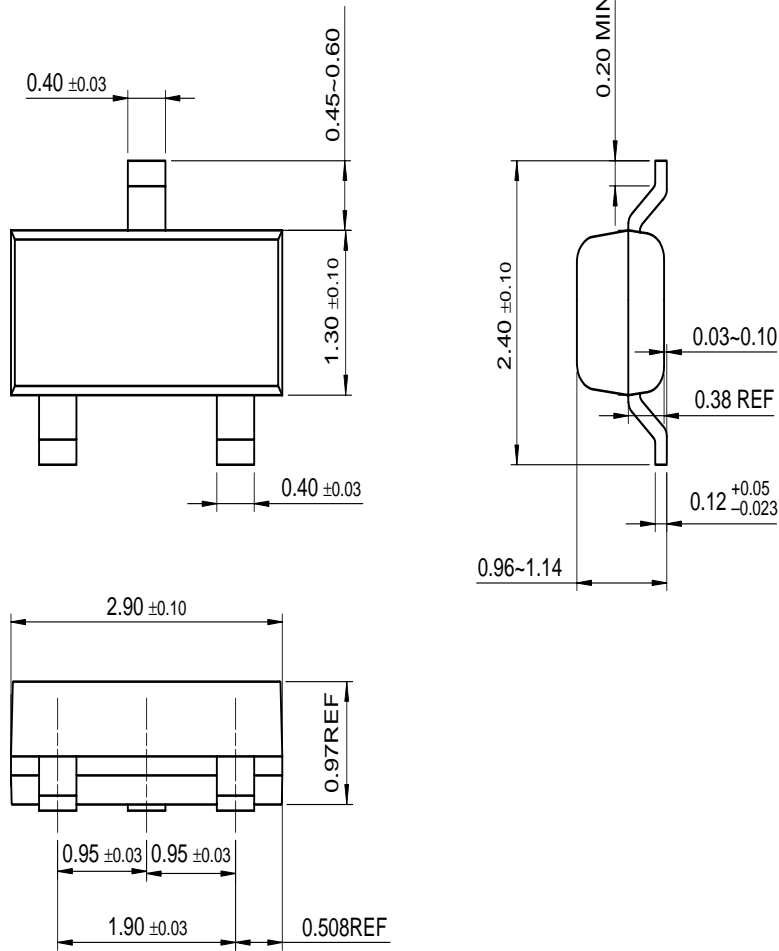


Figure 6. Current Gain Bandwidth Product

Package Dimensions

SOT-23



Dimensions in Millimeters

BC856/857/858/859/860

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